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Docket No. 740819-425

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Haruko INOUE et al.

Serial No. 09/666,156

Filed: September 19, 2000

For: HIGH-VOLTAGE MOS TRANSISTOR  
(AS AMENDED)

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Group Art Unit: 2811

Examiner: Steven Ho Yin Loke

Date: September 6, 2002

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Adm/lt

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on September 6, 2002.

Jeannie M. Saxton

AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated May 8, 2002, the period for response having been extended one (1) month until **September 8, 2002**, the following amendment and remarks are respectfully submitted in connection with the above-identified application.

IN THE TITLE OF THE INVENTION:

Please delete the title of the invention and substitute therefor "HIGH-VOLTAGE MOS TRANSISTOR."

IN THE DRAWINGS:

Please consider the *Request for Approval of Drawing Corrections* concurrently filed

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